

P-Channel Enhancement Mode MOSFET

Feature

-20V/-2A, $R_{DS(ON)} = 120\text{m}\Omega(\text{MAX})$ @ $V_{GS} = -4.5\text{V}$.

$R_{DS(ON)} = 150\text{m}\Omega(\text{MAX})$ @ $V_{GS} = -2.5\text{V}$.

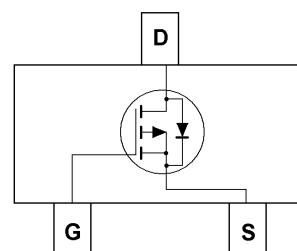
Super High dense cell design for extremely low $R_{DS(ON)}$

Reliable and Rugged

SOT-23 for Surface Mount Package



SOT-23



Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-2	A

Electrical Characteristics

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$	-	-	-1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 10\text{V}, V_{DS} = 0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -10\text{V}, V_{DS} = 0\text{V}$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.4	-	-1.0	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{V}, I_D = -2.0\text{A}$	-	--	120	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -1.5\text{A}$	-	--	150	$\text{m}\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0\text{V}, I_S = -1.25\text{A}$			-1.2	V

Typical Characteristics

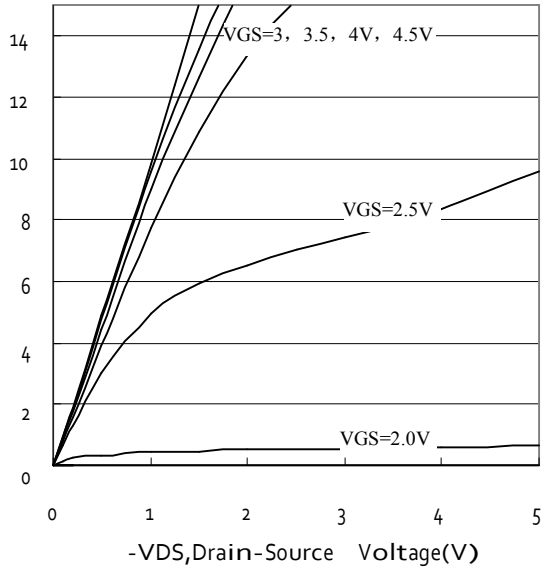


Figure 1. Output Characteristics

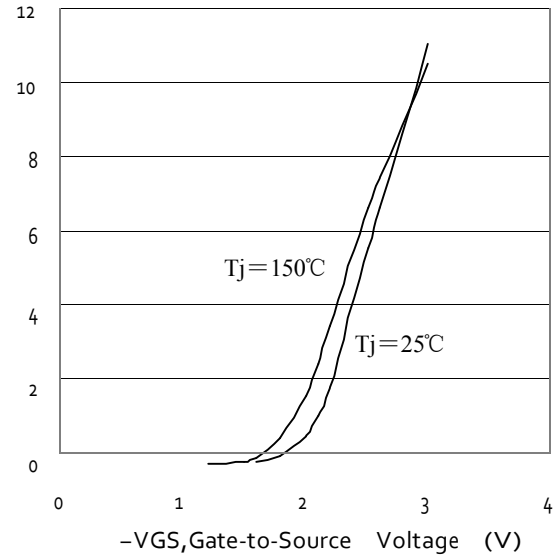


Figure 2. Transfer Characteristics

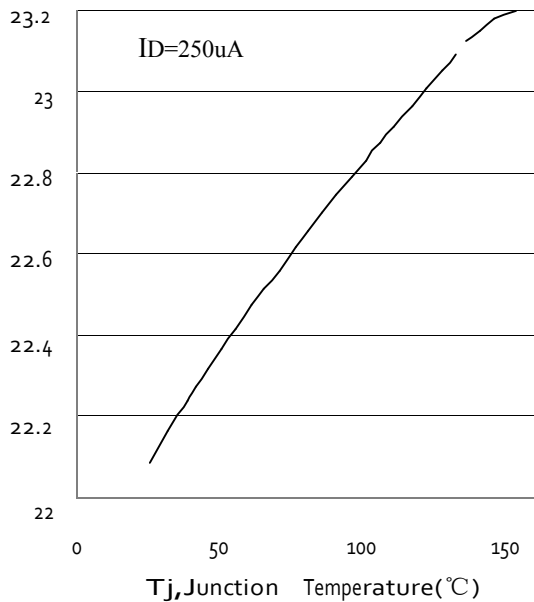


Figure 3. Breakdown Voltage Variation with Temperature

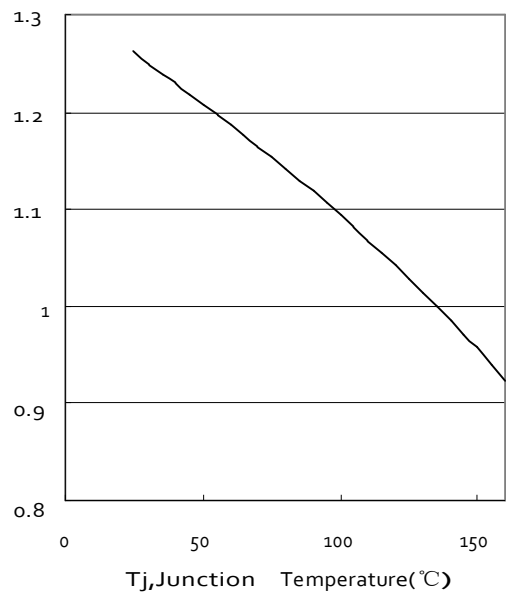


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

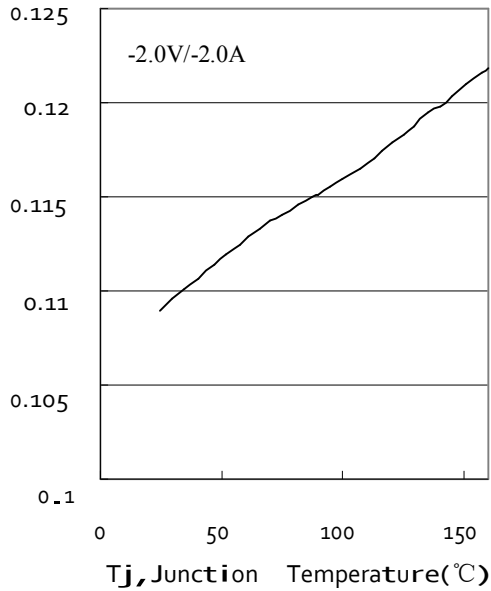


Figure 5. On-Resistance Variation with Temperature

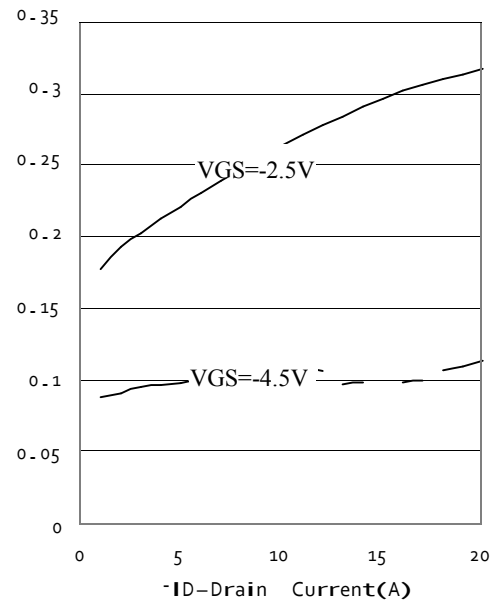


Figure 6. On-Resistance vs. Drain Current

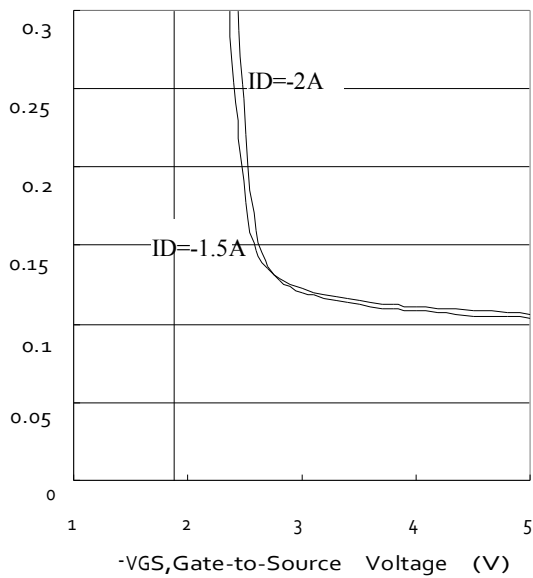


Figure 7. On-Resistance vs. Gate-to-Source Voltage

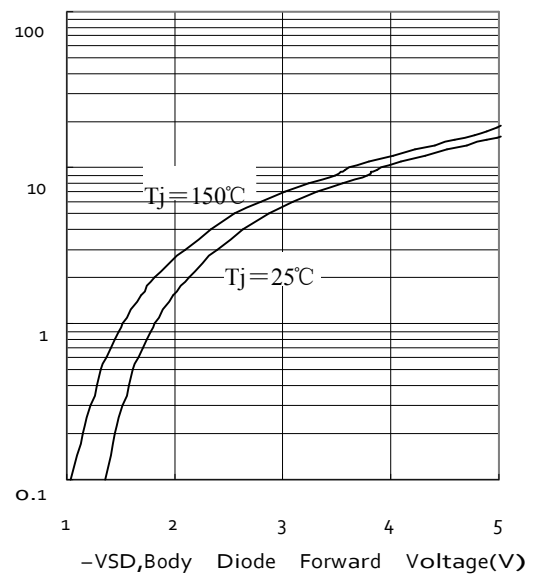
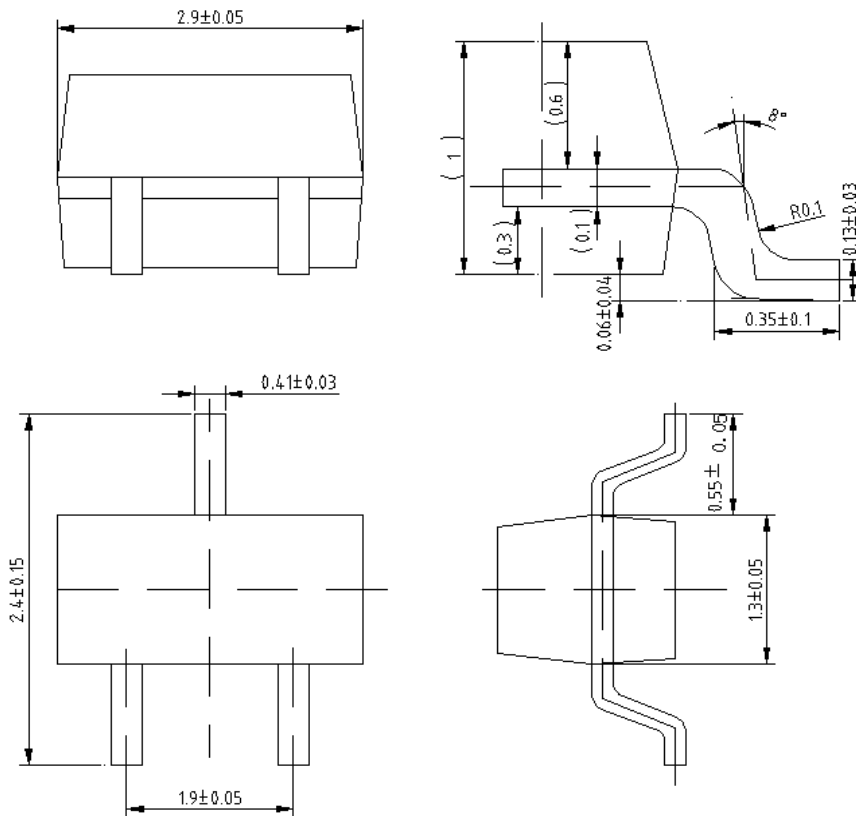


Figure 8. Source-Drain Diode Forward Voltage

Package Outline Dimensions (UNIT: mm)

SOT-23



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Shikues](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#)
[AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)
[C3M0021120D](#)